

國立虎尾科技大學九十八學年度研究所(碩士班)考試入學試題

所別：光電與材料科技研究所

科目：考試科目 2(電子學)

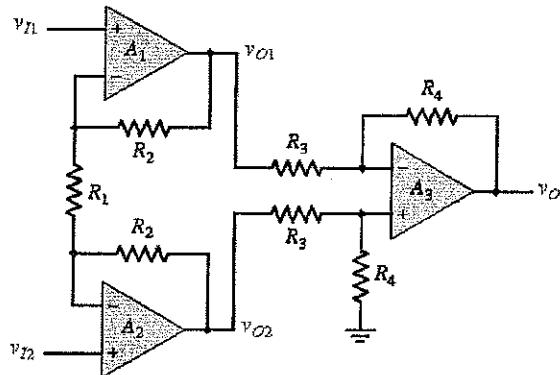
注意事項：

- (1) 共十大題，每題十分。
- (2) 請於答案卷上註明題號。

1. 名詞解釋：(10%)

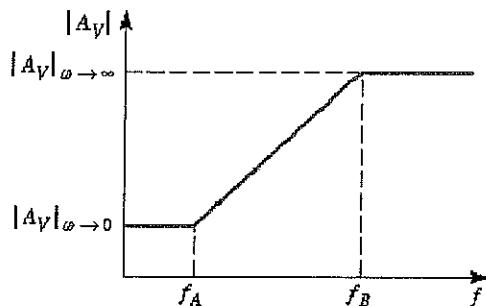
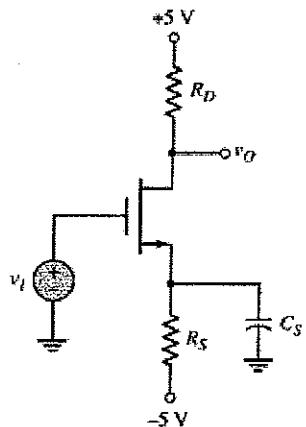
- (a) 何謂 Zener Breakdown ?
- (b) 在金氧半場效電晶體(MOSFET)元件中，何謂反轉層(inversion layer) ?
- (c) 在金氧半場效電晶體(MOSFET)元件中，何謂通道長度調變效應
(channel-length modulation effect) ?
- (d) 在金氧半場效電晶體(MOSFET)元件中，何謂基體效應(body effect) ?

2. 一儀器放大器如圖所示，若電路中的 OP 皆是理想的電路，求此一電路的電壓增益 $v_O/(v_{I1} - v_{I2}) = ?$ (10%)



3. 一放大器電路及其電壓增益(A_V)的波德圖(Bode plot)如下圖，電晶體參數為： $K_n=0.5$ mA/V²， $V_T=0.8$ V， $\lambda=0$ ， $R_D=5.6$ kΩ、 $R_S=6.4$ kΩ， $C_S=5\ \mu F$ 。(10%)

- (a) 求兩個電壓增益 $|A_V|_{\omega \rightarrow \infty}$ 及 $|A_V|_{\omega \rightarrow 0}$ ；(b) 求兩個轉角頻率 f_A 及 f_B 。



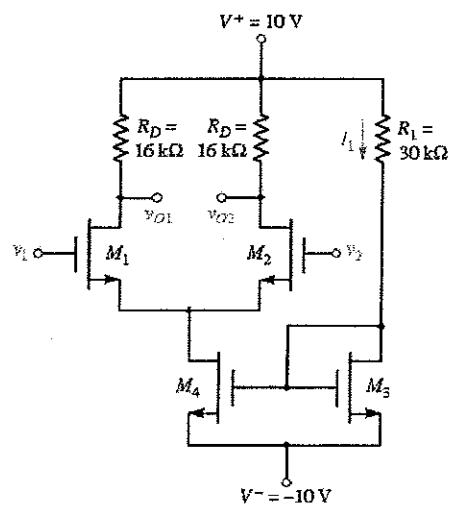
4. 一個差動放大器電路如圖所示，各電晶體皆工作在飽合區(saturation region)，其參數分別為：(10%)

$$K_{n1} = K_{n2} = 1 \text{ mA/V}^2, K_{n3} = K_{n4} = 0.3 \text{ mA/V}^2,$$

$$\lambda = 0, V_{TN} = 1 \text{ V}$$

(a) 求偏壓電流 $I_1 = ?$

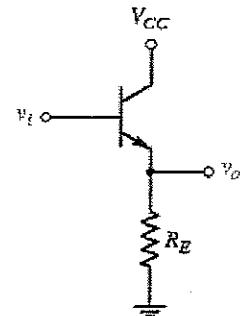
(b) 求差動增益 $(v_{O1} - v_{O2}) / (v_1 - v_2) = ?$



5. 一射極隨耦器(emitter follower)電路如圖所示，(10%)

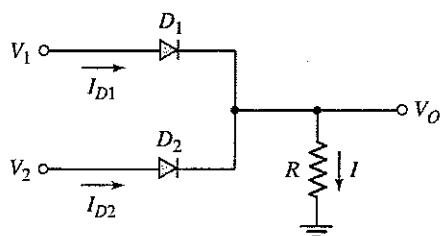
(a) 請問此一電路為何種回授組態？

(b) 此回授組態的回授因子(feedback factor) $\beta = ?$

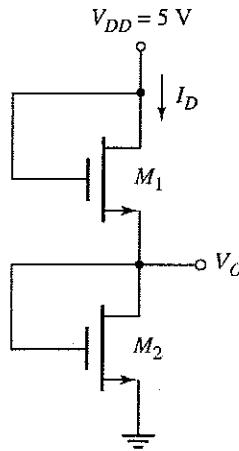


6. (a) Analyze the output voltage, V_O , by V_1, V_2 in following circuit

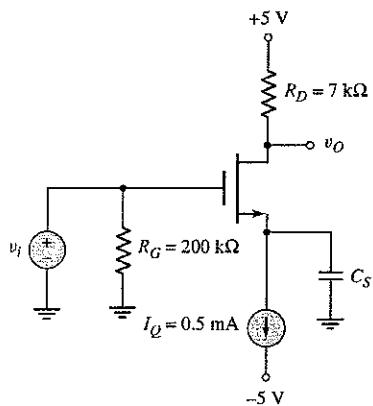
(b) What kind of the logic function for the following circuit (10%)



7. The transistors in the circuit in following figure both have parameters $V_{TN}=0.7V$ and $k_n=30\mu A/V^2$. If the width-to-length ratios of M_1 and M_2 are $(W/L)_1=(W/L)_2=40$, determine V_{GS1} , V_{GS2} , V_O , and I_D (10%)



8. Consider the PMOS common-source circuit in following figure with transistor parameters $V_{TP}=-2V$ and $\lambda=0$, and circuit parameters $R_D=R_L=10 k\Omega$ (a) Determine the value of K_p and R_S such that $V_{SDQ}= 6V$ (b) Determine the resulting value of I_{DQ} and small-signal voltage gain (10%)



9. Consider the bandpass filter in following figure. Show the voltage transfer function is (10%)

$$A_v(s) = \frac{v_o}{v_i} = \frac{\frac{-1}{R_4}}{\frac{1}{R_1} + sC + \frac{1}{sCR_2R_3}}$$

10. Consider the circuit in following figure. The transistors are matched. Assume that base current are negligible and that $V_A=\infty$. If $\beta >> 1$ and the two transistors are identical, show that (10%)

$$I_O R_{E2} - I_{REF} R_{E1} = V_T \ln\left(\frac{I_{REF}}{I_O}\right)$$

